# **Ram Control Block Report**

Interrim report for Code Review

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### **ABSTRACT**

The document contains the initial design and logic for the RAM Control Block designed for the group assignment in the VHDL coursework. RAM Control Block sits between the "Draw Block" and the "VRAM" to act as an interface, manage Read-Modify-Write commands for pixels to be written onto the VRAM which is a 256 word \* 16 bit external RAM.

The RAM control block is an entity that controls which pixel operations need to be stored in the "pixel\_write\_cache" (which will be discussed later in the report) and then store the pixels into the VRAM. The Draw Block will give draw, flush or clear-screen commands to the RAM Control Block.

NB. RCB uses the following files:

- 1) rcb.vhd
- 2) ram fsm.vhd
- 3) pixel\_write\_cache.vhd
- 4) pixel\_word\_cache.vhd

The handshake signals between Draw Block and RCB is shown in the following diagram:

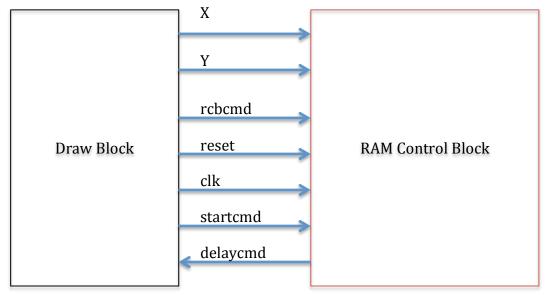


Figure 1

The top-level sketch of the design is shown in the next figure.

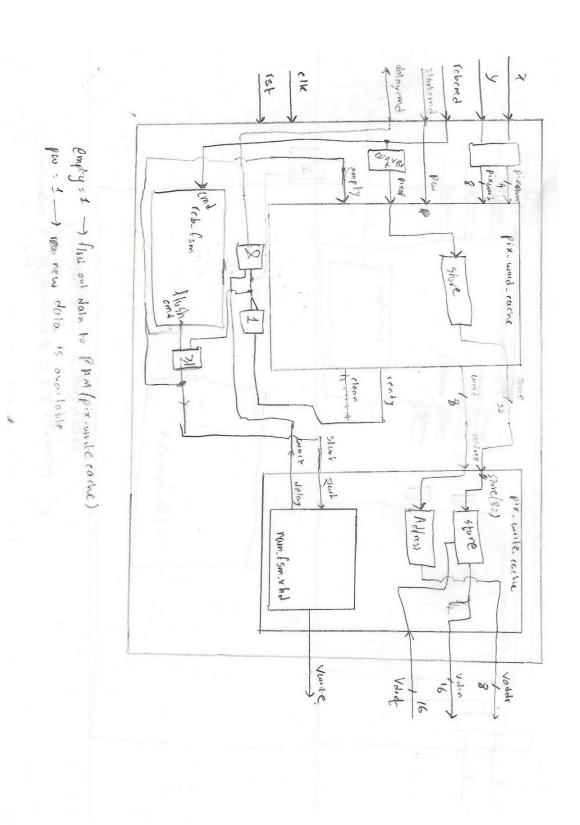


Figure 2

## **Top-design:**

There are three entities that go inside the RAM Control Block as follows:

- 1) pixel\_word\_cache
- 2) pixel write cache
- 3) ram\_fsm

Among the top files, pixel\_word\_cache and ram\_fsm have been already created and tested.

### Pixel\_word\_cache:

The input signals "x" and "y" to the rcb are first converted to represent an 8-bit signal "word" and a 4-bit pixel number called "pixnum" of the pixel\_word\_cache. Then the "rcbcmd" from the draw block is converted to do draw commands if required in that cycle. The input signal to the rcb called "startcmd" is connected directly to the "pw" input of the pixel word cache.

One important thing to notice is that the "ready" signal from the output denotes that the pixel\_word\_cache needs its pixel operations to be flushed into the RAM (depending if the operations aren't clean i.e. the dirty bit is high i.e. the data isn't consistent with the RAM). Therefore in the same cycle the "empty" signal (which is an input to the entity) is set to high so that the flush operation can begin.

### Pixel\_write\_cache & Ram\_fsm:

The main purpose of having this is to reduce the number of cycles to address a large external RAM. This acts like a buffer between the "pixel\_word\_cache" and the RAM. The "pixel\_word\_cache" sees this as another generic RAM.

The "pixel\_write\_cache" includes the entity "ram\_fsm" which does the timing for the RMW (Read-Modify-Write) operation, which takes 3 cycles to complete. Whenever "empty" is asserted, at the same time "start" signal is asserted so that the flushing and writing new operation (once the "ready" signal is set to high) can begin. The "word" output from the "pixel\_word\_cache" acts as the "address" input for this entity and it is stored in an address register, which is clocked at a negative clock edge to **delay** the **address** output by **half a clock cycle**. When the

"empty" signal is asserted, immediately the "store" output from the "pixel\_word\_cache" is stored inside the "store" register of the pixel\_write\_cache. Then the "vdin" output, which is the input to the VRAM is changed according to the stored pixel operations. This output is made sure to be delayed by half a clock cycle.

**Important to notice:** In the beginning it would not be quite intuitive to see that the delay outputs from pixel\_word\_cache (!ready) and pixel\_write\_cache (wait) are **ANDED** together to represent the **delaycmd** output of the rcb. However it makes sense because it can be seen that with this arrangement the "pixel\_word\_cache can still receive some inputs if the Ram\_fsm is completing its RMW operation and so making things more efficient.

### Finite State Machine (RCB):

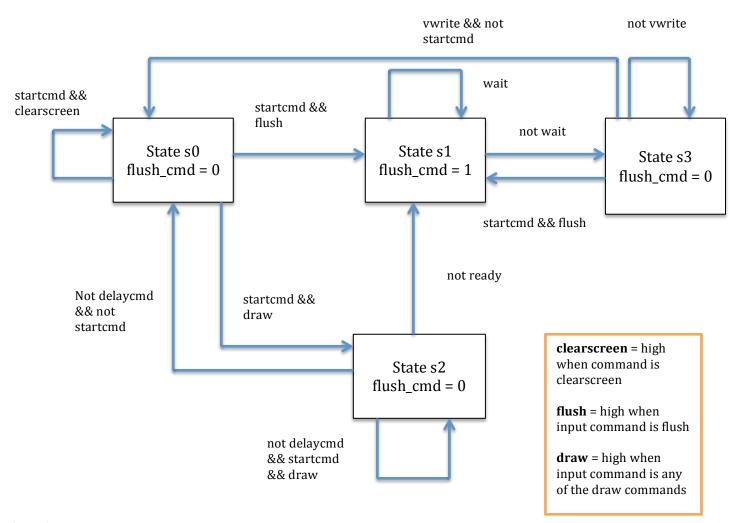


Figure 3

Figure 3 show the Finite State Machine for the Ram Control Block.

The following table outlines the truth table for the FSM shown in figure 3

Curre	reset	startcmd	delay	Rea	Flus	Dra	Clearscee	vwrit	wait	nextstate	flush_cm
nt			cmd	dy	h	w	n	е			d
state											
SX	1	Х	Х	Χ	Х	Χ	Х	Χ	Χ	S0	0
S0	0	1	Х	Χ	1	Χ	Х	Χ	Χ	S1	1
S0	0	1	Χ	Χ	Χ	Χ	1	Χ	Χ	SO SO	0
S0	0	1	Χ	Χ	X	1	Χ	Χ	Χ	S2	0
S1	0	Χ	Χ	Χ	X	Χ	Χ	Χ	1	S1	1
S1	0	Χ	Χ	Χ	X	Χ	Χ	Χ	0	S3	0
S2	0	1	0	Χ	X	1	Χ	Χ	Χ	S2	0
S2	0	Χ	Χ	0	X	Χ	Χ	Χ	Χ	S1	1
S2	0	0	0	Χ	Х	Х	Χ	Χ	Х	SO	0
S3	0	1	Χ	Χ	1	Χ	Χ	Χ	Χ	S1	1
S3	0	0	Χ	Χ	Х	Χ	Χ	1	Χ	SO	0
<b>S</b> 3	0	Χ	Χ	Χ	Х	Χ	Χ	0	Χ	S3	0

# **Entities in terms of process blocks (Code):**

**NB:** The functionalities for the already written entities (pix\_word\_cache and ram\_fsm) are not included as they remain as they were (except additions for Generics).

### rcb.vhd:

The rcb has the following process blocks:

<u>P1:</u> Process "P1" is a combinatorial process where the x,y and rcb command inputs are computed and then fed into the pixel\_word\_cache block.

Driven outputs:

- 1) pixword
- 2) pixnum

<u>P2:</u> Process "P2" is a combinatorial process where the next state is assigned depending on current inputs and current state. The outputs that are driven are as follows:

Driven outputs:

1) nstate

<u>C1:</u> Process "C1" is a clocked process and in this state, the current state is driven by whatever nexstate was form previous cycle.

Drive outputs:

1) state

### pix\_write\_cache.vhd:

<u>address\_delay:</u> Waits till falling edge of clock to ensure half a cycle delay and then assigns the output "vaddr" to the current address. This is a clocked process.

Driven outputs: 1) vaddr

<u>din\_compute</u>: This is a clocked process. In half a cycle after vwrite, this assigns the value of din according to the current pixel operations.

Driven outputs:

1) vdin

### How to do clearscreen?

At the moment the blocks aren't designed to handle clearscreen commands. However I do have an idea of how to do the clearscreen command.

Firstly I have to create a FIFO for the instructions so that all the instructions get stored inside the FIFO and read off the other end at the same time. So when there is a clearscreen command, the previous values of x and y need to be taken and the new values to of x1 and y1 to which the screen should be cleared. Then the delaycmd should be kept high. While the delaycmd is high, the RCB should create instructions

itself to write white or black depending on clearscreen instruction. These commands should be stored in the FIFO and the delaycmd should only be low when these instructions have been made and the system can recover back from stall.

# Ram Control Block Code Review

Jonathan Ely

November 25, 2011

## 1 Code Correctness

Blah